100V P-Channel Trench Power MOSFET

General Description

The SJP01P820 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

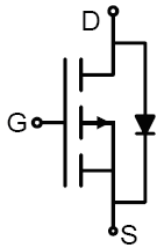
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

Application

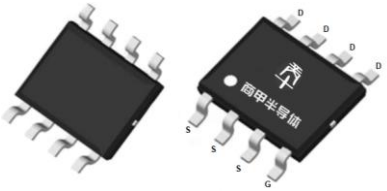
- Power Management Switches
- Portable equipment and battery powered systems

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	-100	V
$R_{DS(ON)\_TYP}$	80	mΩ
I_D	-5	A
Q_G	35	nC



Schematic Diagram



SOP-8 top&bottom view

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJP01P820	SJP01P820	SOP-8	Tape	\	\	4000 Pcs

Table 1. Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	-100	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
I_D	Drain Current-Continuous(T_A=25℃)	-5	A
	Drain Current-Continuous(T_A=100℃)	-3.2	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	-20	A
P_D	Maximum Power Dissipation(T_A=25℃)	5.4	W
	Maximum Power Dissipation(T_A=100℃)	2.2	W
E_{AS}	Avalanche energy (Note 2)	210	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-100V, V_{GS}=0V T_J=25℃			-1	μA
		V_{DS}=-100V, V_{GS}=0V T_J=125℃			-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1		-2.5	V
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-10A		26		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-10A T_J=25℃		80	100	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-4.5V, I_D=-8A T_J=25℃		86	114	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-50V, V_{GS}=0V, f=1.0MHz		3769		pF
C_{oss}	Output Capacitance			72.3		pF
C_{rss}	Reverse Transfer Capacitance			66.4		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		4.7		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=-10V, V_{DS}=-50V, R_L=5Ω, R_{GEN}=9.1Ω		11.6		nS
t_r	Turn-on Rise Time			17.6		nS
$t_{d(off)}$	Turn-Off Delay Time			48		nS
t_f	Turn-Off Fall Time			20		nS
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-50V, I_D=-10A		35		nC
Q_{gs}	Gate-Source Charge			8.4		nC
Q_{gd}	Gate-Drain Charge			9.3		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				-5	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=-10A			-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-10A, di/dt=100A/μs		24.9		ns
Q_{rr}	Reverse Recovery Charge	I_F=-10A, di/dt=100A/μs		128.8		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=50V,V_G=-10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

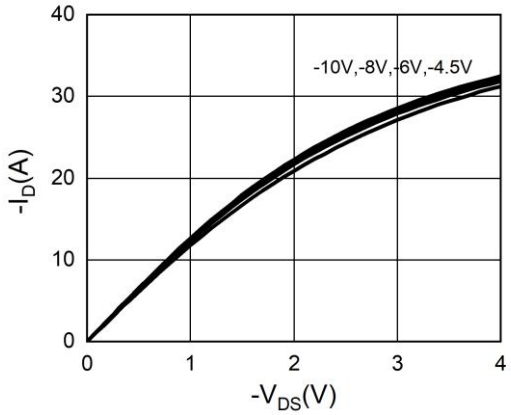


Figure 2. Transfer Characteristics

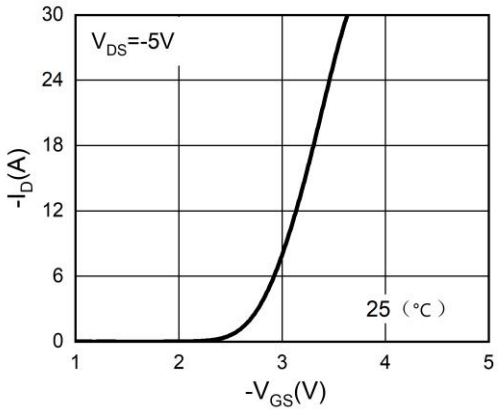


Figure 3. Power Dissipation

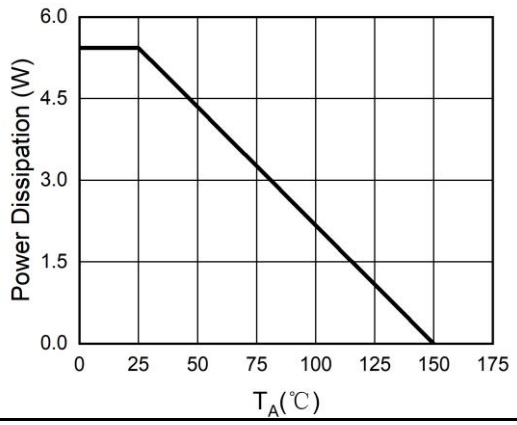


Figure 4. Drain Current

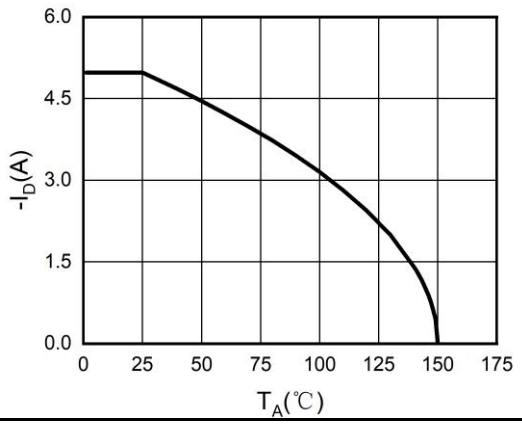


Figure 5. BV_{DSS} vs Junction Temperature

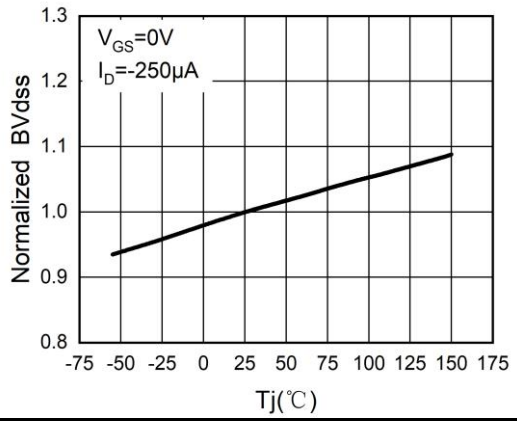
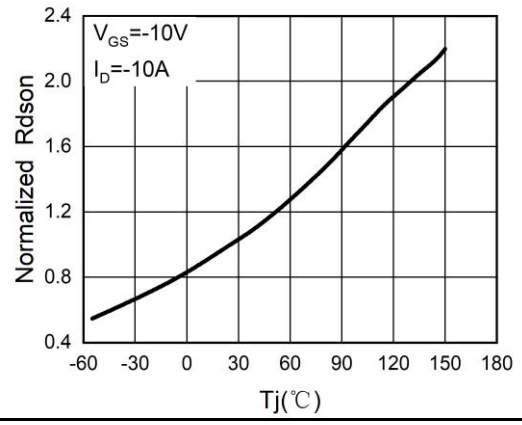


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

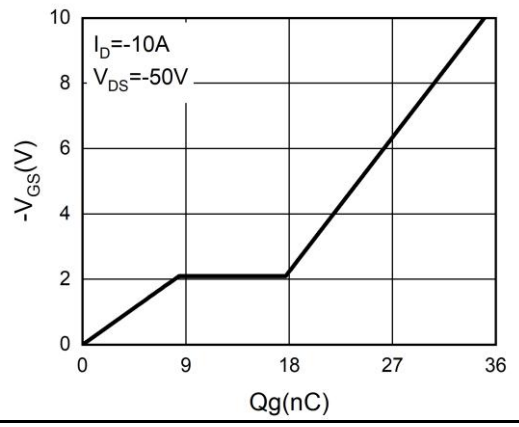


Figure 8. Capacitance

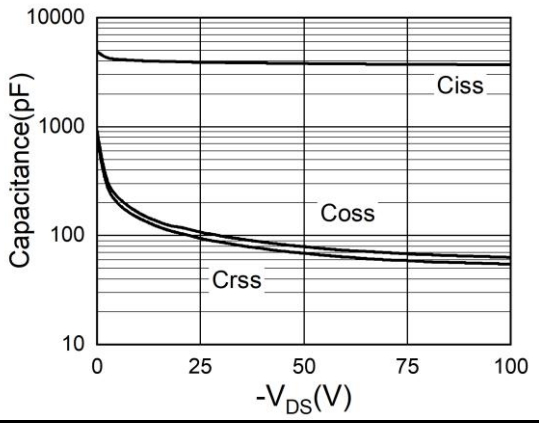


Figure 9. Body-Diode Characteristics

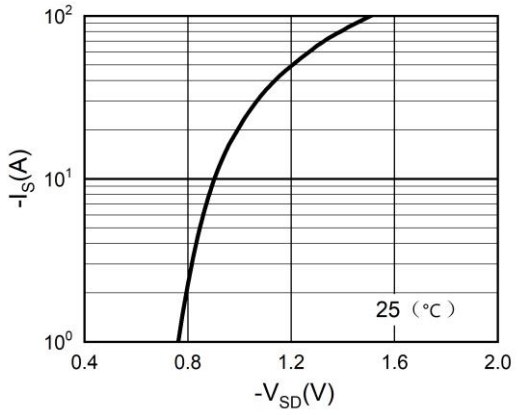
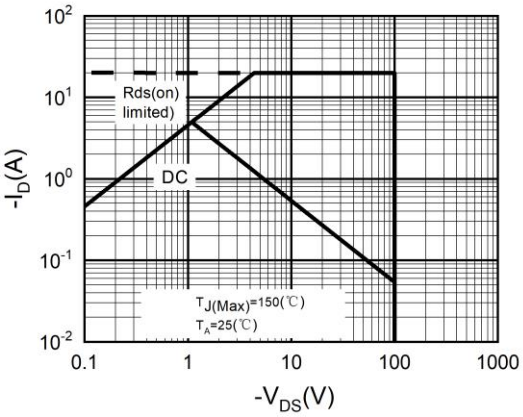
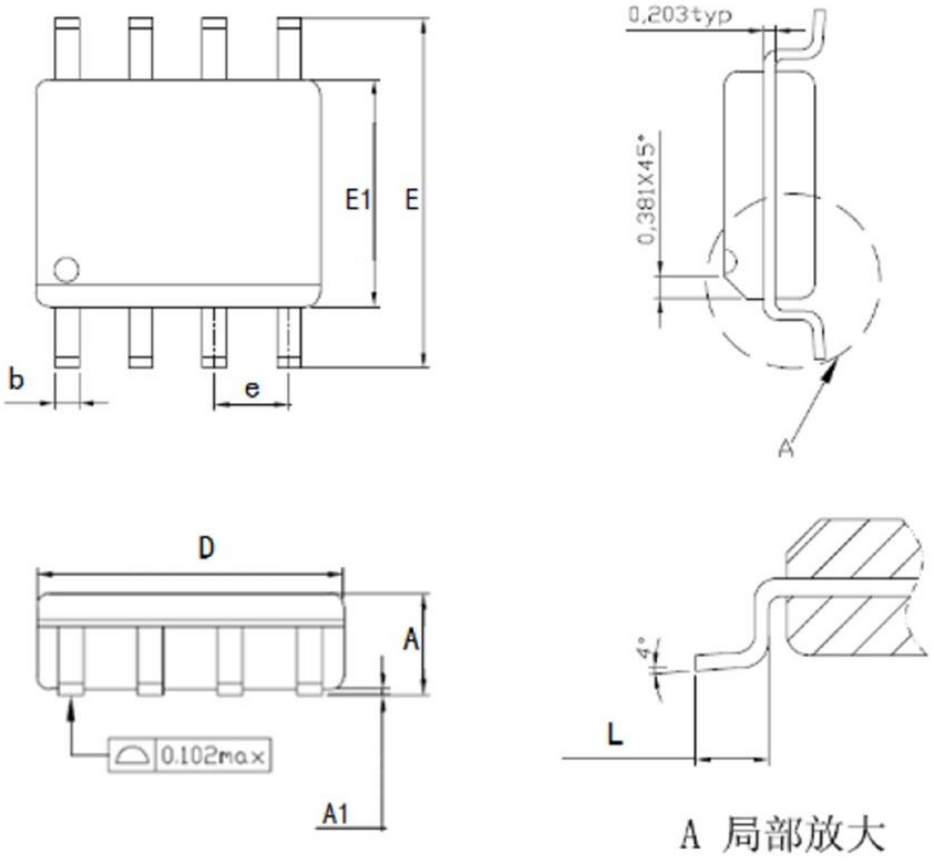


Figure 10. Maximum Safe Operating Area



SOP-8 Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max
A	1.35	1.55	1.75
A1	0.1	0.15	0.2
b	0.346	0.406	0.466
D	4.8	4.89	4.98
E	5.75	6.00	6.25
E1	3.81	3.90	3.99
e	1.27TYP		
L	0.406	0.838	1.27

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